SN74AC573-Q1 Automotive Octal Transparent D-Type Latches With 3-State Outputs

1 Features

- AEC-Q100 qualified for automotive applications:
  - Device temperature grade 1: -40°C to +125°C
  - Device HBM ESD classification level 2
  - Device CDM ESD classification level C4B
- Wide operating range of 1.5V to 6V
- Inputs accept voltages up to 6V
- Continuous ±24mA output drive at 5V
- Supports up to ±75mA output drive at 5V in short bursts
- Drives 50Ω transmission lines
- Maximum t_{pd} of 7.9ns at 5V, 50pF load

2 Applications

- Parallel data storage
- Digital bus buffer

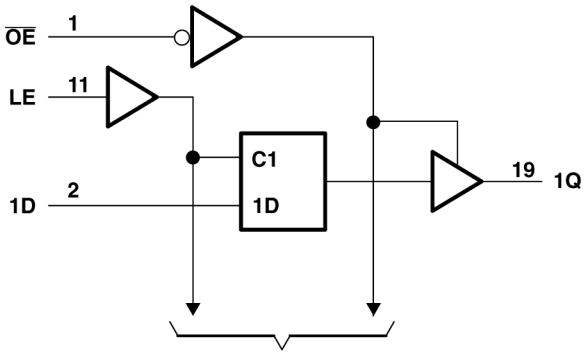
3 Description

The SN74AC573-Q1 contains eight transparent D-type latches with shared 3-state output and latch control.

Package Information

PART NUMBER	PACKAGE(1)	PACKAGE SIZE(2)	BODY SIZE(3)
SN74AC573-Q1	PW (TSSOP, 20)	6.5 mm × 6.4 mm	6.50mm x 4.40mm
	RKS (WQFN, 20)	4.5 mm × 2.5 mm	4.5 mm × 2.5 mm

(1) For more information, see Section 10.
(2) The package size (length × width) is a nominal value and includes pins, where applicable
(3) The body size (length × width) is a nominal value and does not include pins.



Logic Diagram (Positive Logic)

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4 Pin Configuration and Functions

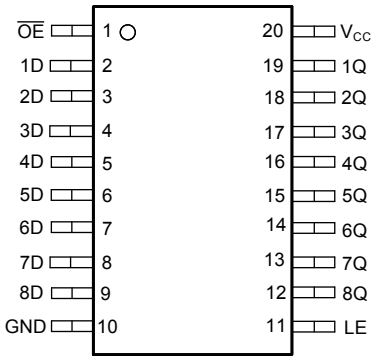

Figure 4-1. SN74AC573-Q1 PW Package, 20-Pin TSSOP (Top View)

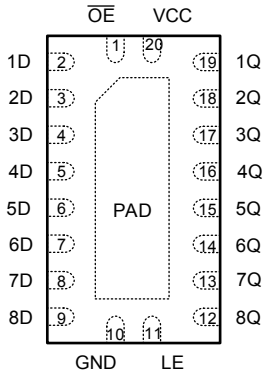

Figure 4-2. RKS Package, 20-Pin VQFN (Top View)

Table 4-1. Pin Functions

PIN		TYPE[1]	DESCRIPTION
NAME	NO.		
$\overline{OE}$	1	I	Output enable
1D	2	I	1D input
2D	3	I	2D input
3D	4	I	3D input
4D	5	I	4D input
5D	6	I	5D input
6D	7	I	6D input
7D	8	I	7D input
8D	9	I	8D input
GND	10	G	Ground
LE	11	I	Latch enable input
8Q	12	O	8Q output
7Q	13	O	7Q output
6Q	14	O	6Q output
5Q	15	O	5Q output
4Q	16	O	4Q output
3Q	17	O	3Q output
2Q	18	O	2Q output
1Q	19	O	1Q output
V_{CC}	20	P	Positive supply
Thermal pad[2]		—	The thermal pad can be connected to GND or left floating. Do not connect to any other signal or supply

(1) I = Input, O = Output, I/O = Input or Output, G = Ground, P = Power.
(2) RKS package only.

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5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage range		-0.5	7	V
V_I	Input voltage range(2)		-0.5	V_{CC} + 0.5 V	V
V_O	Output voltage range(2)		-0.5	V_{CC} + 0.5 V	V
I_{IK}	Input clamp current	V_I < -0.5 V or V_I > V_{CC} + 0.5 V		±20	mA
I_{OK}	Output clamp current	V_O < -0.5 V or V_O > V_{CC} + 0.5 V		±50	mA
I_O	Continuous output current	V_O = 0 to V_{CC}		±50	mA
	Continuous output current through V_{CC} or GND			±200	mA
T_{stg}	Storage temperature		-65	150	°C

(1) Operation outside the *Absolute Maximum Ratings* may cause permanent device damage. Absolute maximum ratings do not imply functional operation of the device at these or any other conditions beyond those listed under *Recommended Operating Conditions*. If briefly operating outside the *Recommended Operating Conditions* but within the *Absolute Maximum Ratings*, the device may not sustain damage, but it may not be fully functional. Operating the device in this manner may affect device reliability, functionality, performance, and shorten the device lifetime.
(2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

5.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per AEC Q100-002 HBM ESD Classification Level 2(1)	±2000	V
		Charged device model (CDM), per AEC Q100-011 CDM ESD Classification Level C4B	±1000	

(1) AEC Q100-002 indicate that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

Specification	Description	Condition	MIN	MAX	UNIT
V_{CC}	Supply voltage		1.5	6	V
V_{IH}	High-level input voltage	V_{CC} = 1.5 V	1.2		V
		V_{CC} = 1.8 V	1.26		
		V_{CC} = 2.5 V	1.75		
		V_{CC} = 3 V	2.1		
		V_{CC} = 4.5 V	3.15		
		V_{CC} = 5.5 V	3.85		
V_{IL}	Low-Level input voltage	V_{CC} = 1.5 V		0.3	V
		V_{CC} = 1.8 V		0.54	
		V_{CC} = 2.5 V		0.75	
		V_{CC} = 3 V		0.9	
		V_{CC} = 4.5 V		1.35	
		V_{CC} = 5.5 V		1.65	
V_I (1)	Input Voltage		0	V_{CC}	V
V_O	Output Voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 1.8 V		-1	mA
		V_{CC} = 2.5 V		-2	
		V_{CC} = 3.3 V		-12	
		V_{CC} = 5 V		-24	

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5.3 Recommended Operating Conditions (continued)

over operating free-air temperature range (unless otherwise noted)

Specification	Description	Condition	MIN	MAX	UNIT
I_{OL}	Low-level output current	V_{CC} = 1.8 V		1	mA
		V_{CC} = 2.5 V		2	
		V_{CC} = 3.3 V		12	
		V_{CC} = 5 V		24	
Δt/Δv	Input transition rise or fall rate	1.5 V ≤ V_{CC} ≤ 3 V		50	ns/V
		3 V < V_{CC} ≤ 5.5 V		20	
T_A	Operating free-air temperature		-40	125	°C

(1) All unused inputs of the device must be held at VCC or GND for proper device operation. Refer to the TI application report *Implications of Slow or Floating CMOS Inputs*.

5.4 Thermal Information

THERMAL METRIC(1)		PW (TSSOP)	RKS (VQFN)	UNIT
		20 PINS	20 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	126.2	72.9	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	68.7	77.1	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	77.3	45.6	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	22.3	13.2	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	76.9	45.6	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	29.4	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

5.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted); typical values measured at T_A = 25°C

PARAMETER	TEST CONDITIONS	V_{CC}	MIN	TYP	MAX	UNIT
V_{OH}	I_{OH} = -50μA	1.5 V	1.4	1.49		V
		1.8 V	1.7	1.79		
		2.5 V	2.4	2.49		
		3 V	2.9	2.99		
		4.5 V	4.4	4.49		
		5.5 V	5.4	5.49		
	I_{OH} = -1mA	1.8 V	1.44			
	I_{OH} = -2mA	2.5 V	2			
	I_{OH} = -4mA	3 V	2.4			
	I_{OH} = -12mA	3 V	2.4			
	I_{OH} = -24mA	4.5 V	3.7			
	I_{OH} = -24mA	5.5 V	4.7			
	I_{OH} = -75mA	5.5 V				
	I_{OH} = -50mA	5.5 V	3.85			

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5.5 Electrical Characteristics (continued)

over operating free-air temperature range (unless otherwise noted); typical values measured at T_A = 25°C

PARAMETER	TEST CONDITIONS	V_{CC}	MIN	TYP	MAX	UNIT
V_{OL}	I_{OL} = 50µA	1.5 V		0.01	0.1	V
		1.8 V		0.01	0.1	
		2.5 V		0.01	0.1	
		3 V		0.01	0.1	
		4.5 V		0.01	0.1	
		5.5 V		0.01	0.1	
	I_{OL} = 1mA	1.8 V			0.36	
	I_{OL} = 2mA	2.5 V			0.5	
	I_{OL} = 4mA	3 V			0.5	
	I_{OL} = 12mA	3 V			0.5	
	I_{OL} = 24mA	4.5 V			0.5	
	I_{OL} = 24mA	5.5 V			0.5	
	I_{OL} = 50mA	5.5 V			1.65	
	I_{OL} = 75mA	5.5 V			1.65	
I_I	V_I = 5.5 V or GND	0 V to 5.5 V			±1	µA
I_{OZ}	V_O = V_{CC} or GND	5.5 V			±5	µA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	5.5 V			20	µA
C_I	V_I = V_{CC} or GND	5 V		9		pF
C_O	V_O = V_{CC} or GND	5 V		15		pF
C_{PD} (1) (2)	F = 1MHz	5 V		60		pF

(1) C_{PD} is used to determine the dynamic power consumption, per channel
(2) $P_D = V_{CC}^2 \times F_I \times (C_{PD} + C_L)$ where F_I= input frequency, C_L= output load capacitance, V_{CC}= supply voltage

5.6 Timing Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	DESCRIPTION	CONDITION	V_{CC}	T_A = 25°C		-40°C to 85°C		-40°C to 125°C		UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		1.5 V		15		11		10	MHz
t_W	Pulse duration	LE high	1.5 V	44		44		50		ns
t_W	Pulse duration	CLK high or low	1.5 V	44		44		50		ns
t_W	Pulse duration	CLR low	1.5 V	35		55		63		ns
t_{SU}	Setup time	Data before LE↓	1.5 V	2		2		2		ns
t_{SU}	Setup time	CLR inactive	1.5 V	2		2		2		ns
t_{SU}	Setup time	Data before CLK↑	1.5 V	2		2		2		ns
t_H	Hold time	Data after CLK↑	1.5 V	2		2		2		ns
t_H	Hold time	Data after LE↓	1.5 V	15		33		38		ns
f_{clock}	Clock frequency		1.8 V		55		45		44	MHz
t_W	Pulse duration	LE high	1.8 V	7.2				11.4		ns
t_W	Pulse duration	CLK high or low	1.8 V	8.6				12.6		ns
t_W	Pulse duration	CLR low	1.8 V	6.5				10.9		ns
t_{SU}	Setup time	Data before LE↓	1.8 V	5.1				5.6		ns
t_{SU}	Setup time	CLR inactive	1.8 V	5.3				5.4		ns

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5.6 Timing Characteristics (continued)

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	DESCRIPTION	CONDITION	V_{CC}	T_A = 25°C		-40°C to 85°C		-40°C to 125°C		UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	
t_{SU}	Setup time	Data before CLK↑	1.8 V	8.3				9.5		ns
t_H	Hold time	Data after CLK↑	1.8 V	2				2		ns
t_H	Hold time	Data after LE↓	1.8 V	2				2		ns
f_{clock}	Clock frequency		2.5 V		90		78		65	MHz
t_W	Pulse duration	LE high	2.5 V	6				6		ns
t_W	Pulse duration	CLK high or low	2.5 V	7.3				7.3		ns
t_W	Pulse duration	CLR low	2.5 V	6				6		ns
t_{SU}	Setup time	Data before LE↓	2.5 V	2.4				2.8		ns
t_{SU}	Setup time	CLR inactive	2.5 V	2.5				2.8		ns
t_{SU}	Setup time	Data before CLK↑	2.5 V	3.9				7.5		ns
t_H	Hold time	Data after CLK↑	2.5 V	1				1		ns
t_H	Hold time	Data after LE↓	2.5 V	2				2.3		ns
f_{clock}	Clock frequency		3.3 V		101		89		75	MHz
t_W	Pulse duration	LE high	3.3 V	5.5		4.9		5.6		ns
t_W	Pulse duration	CLK high or low	3.3 V	5		4.9		5.6		ns
t_W	Pulse duration	CLR low	3.3 V			6.1		7		ns
t_{SU}	Setup time	Data before LE↓	3.3 V	3.5		2		2		ns
t_{SU}	Setup time	CLR inactive	3.3 V			2		2		ns
t_{SU}	Setup time	Data before CLK↑	3.3 V	2.5		2		2		ns
t_H	Hold time	Data after CLK↑	3.3 V	1		1		1		ns
t_H	Hold time	Data after LE↓	3.3 V	2		2		4.2		ns
f_{clock}	Clock frequency		5 V		150		143		125	MHz
t_W	Pulse duration	LE high	5 V	4		3.5		4		ns
t_W	Pulse duration	CLK high or low	5 V	3.5		3.5		4		ns
t_W	Pulse duration	CLR low	5 V			4.4		5		ns
t_{SU}	Setup time	Data before LE↓	5 V	3		2		2		ns
t_{SU}	Setup time	CLR inactive	5 V			2		2		ns
t_{SU}	Setup time	Data before CLK↑	5 V	1.5		2		2		ns
t_H	Hold time	Data after CLK↑	5 V	1		1.5		2		ns
t_H	Hold time	Data after LE↓	5 V	1		1		1		ns

5.7 Switching Characteristics

C_L = 50pF; over operating free-air temperature range; typical values measured at T_A = 25°C (unless otherwise noted).
See *Parameter Measurement Information*

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC}	T_A = 25°C			-40°C to 85°C			-40°C to 125°C			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
t_{PLH}	D	Q	1.5 V		18.2	31.9			33.4			34.1	ns
t_{PHL}	D	Q	1.5 V		19.5	32.6			34			34.4	ns
t_{PLH}	LE	Q	1.5 V		21.9	38.2			39.8			40.6	ns
t_{PHL}	LE	Q	1.5 V		22.1	37.6			39.2			39.7	ns

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5.7 Switching Characteristics (continued)

C_L = 50pF; over operating free-air temperature range; typical values measured at T_A = 25°C (unless otherwise noted).
See *Parameter Measurement Information*

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC}	T_A = 25°C			-40°C to 85°C			-40°C to 125°C			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
t_{PZH}	$\overline{OE}$	Q	1.5 V		17.4	29.3			30.6			31.3	ns
t_{PZL}	$\overline{OE}$	Q	1.5 V		18.3	30.7			31.6			31.9	ns
t_{PHZ}	$\overline{OE}$	Q	1.5 V		22.6	32.2			33.2			33.7	ns
t_{PLZ}	$\overline{OE}$	Q	1.5 V		14.2	21.2			21.6			21.7	ns
t_{PLH}	CLK	Q	1.5 V		21.8	44			45.9			46.5	ns
t_{PHL}	CLK	Q	1.5 V		22.2	41.8			43.6			44.5	ns
t_{PHL}	$\overline{CLR}$	Q	1.5 V		21.5	35.1			36.5			37	ns
t_{PLH}	D	Q	1.8 V		12.6	20.1			22			23	ns
t_{PHL}	D	Q	1.8 V		14	21.7			23.4			24.4	ns
t_{PLH}	LE	Q	1.8 V		15.5	24.6			26.7			27.8	ns
t_{PHL}	LE	Q	1.8 V		16	25			26.9			28.1	ns
t_{PZH}	$\overline{OE}$	Q	1.8 V		12.5	19.3			20.9			21.9	ns
t_{PZL}	$\overline{OE}$	Q	1.8 V		13.6	20.9			22.2			22.9	ns
t_{PHZ}	$\overline{OE}$	Q	1.8 V		17.9	23.9			25.6			26.4	ns
t_{PLZ}	$\overline{OE}$	Q	1.8 V		10.9	14.8			15.3			15.6	ns
t_{PLH}	CLK	Q	1.8 V		15.4	28.1			30.5			31.8	ns
t_{PHL}	CLK	Q	1.8 V		16	27.4			29.8			31.1	ns
t_{PHL}	$\overline{CLR}$	Q	1.8 V		15.7	23.7			25.5			26.4	ns
t_{PLH}	D	Q	2.5 V		7.8	11.3			12.8			13.8	ns
t_{PHL}	D	Q	2.5 V		8.8	12.6			13.9			14.7	ns
t_{PLH}	LE	Q	2.5 V		9.6	14.2			16			17.1	ns
t_{PHL}	LE	Q	2.5 V		10	14.4			16			16.9	ns
t_{PZH}	$\overline{OE}$	Q	2.5 V		8.1	11.6			13			13.9	ns
t_{PZL}	$\overline{OE}$	Q	2.5 V		9.2	13.4			14.5			15.2	ns
t_{PHZ}	$\overline{OE}$	Q	2.5 V		7.8	10.3			11.3			11.7	ns
t_{PLZ}	$\overline{OE}$	Q	2.5 V		5.7	7.6			8.4			8.8	ns
t_{PLH}	CLK	Q	2.5 V		9.6	16.1			18			19.2	ns
t_{PHL}	CLK	Q	2.5 V		9.9	15.7			17.5			18.5	ns
t_{PHL}	$\overline{CLR}$	Q	2.5 V		10	13.8			15.2			16	ns
t_{PLH}	D	Q	3.3 V		6.4	9			10.3			11.1	ns
t_{PHL}	D	Q	3.3 V		7.4	10.2			11.3			12.1	ns
t_{PLH}	LE	Q	3.3 V		8	11.3			12.8			13.8	ns
t_{PHL}	LE	Q	3.3 V		8.4	11.7			13			13.8	ns
t_{PZH}	$\overline{OE}$	Q	3.3 V		6.9	9.5			10.6			11.4	ns
t_{PZL}	$\overline{OE}$	Q	3.3 V		7.6	10.9			11.9			12.5	ns
t_{PHZ}	$\overline{OE}$	Q	3.3 V		6.4	8.4			9.2			9.7	ns
t_{PLZ}	$\overline{OE}$	Q	3.3 V		4.9	6.5			7			7.5	ns
t_{PLH}	CLK	Q	3.3 V		8	12.6			14.3			15.4	ns
t_{PHL}	CLK	Q	3.3 V		8.3	12.6			14.3			15.2	ns
t_{PHL}	$\overline{CLR}$	Q	3.3 V		8.4	11.3			12.4			13.3	ns
t_{PLH}	D	Q	5 V		4.8	6.2			7.1			7.7	ns
t_{PHL}	D	Q	5 V		5.4	7.1			7.9			8.4	ns

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5.7 Switching Characteristics (continued)

C_L = 50pF; over operating free-air temperature range; typical values measured at T_A = 25°C (unless otherwise noted).
See *Parameter Measurement Information*

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC}	T_A = 25°C			-40°C to 85°C			-40°C to 125°C			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
t_{PLH}	LE	Q	5 V		6	7.9			8.9			9.6	ns
t_{PHL}	LE	Q	5 V		6.2	8.2			9.1			9.7	ns
t_{PZH}	$\overline{OE}$	Q	5 V		5.3	6.9			7.7			8.3	ns
t_{PZL}	$\overline{OE}$	Q	5 V		5.5	7.5			8.2			8.7	ns
t_{PHZ}	$\overline{OE}$	Q	5 V		5.1	6.4			6.9			7.3	ns
t_{PLZ}	$\overline{OE}$	Q	5 V		3.6	4.5			5.1			5.4	ns
t_{PLH}	CLK	Q	5 V		6	8.7			9.8			10.6	ns
t_{PHL}	CLK	Q	5 V		6.2	8.8			9.9			10.6	ns
t_{PHL}	$\overline{CLR}$	Q	5 V		6.4	8			8.8			9.4	ns

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6 Detailed Description

6.1 Overview

The eight latches are D-type transparent latches. When the latch-enable (LE) input is high, the Q outputs follow the data (D) inputs. When LE is taken low, the Q outputs are latched at the logic levels set up at the D Inputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or the high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines in a bus-organized system without need for interface or pullup components.

$\overline{OE}$ does not affect the internal operations of the latches. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

6.2 Functional Block Diagram

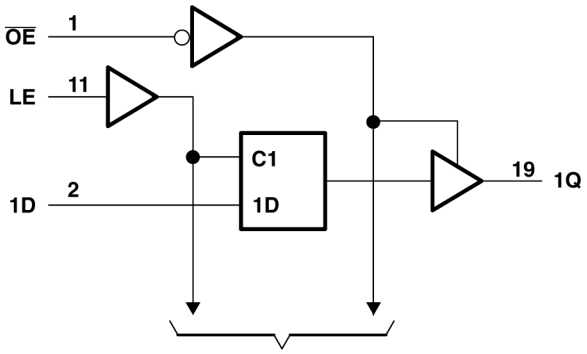

Figure 6-1. Logic Diagram (Positive Logic)

6.3 Feature Description

6.3.1 Balanced CMOS 3-State Outputs

This device includes balanced CMOS 3-state outputs. Driving high, driving low, and high impedance are the three states that these outputs can be in. The term *balanced* indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads, so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device can drive larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

When placed into the high-impedance state, the output will neither source nor sink current, with the exception of minor leakage current as defined in the *Electrical Characteristics* table. In the high-impedance state, the output voltage is not controlled by the device and is dependent on external factors. If no other drivers are connected to the node, then this is known as a floating node and the voltage is unknown. A pull-up or pull-down resistor can be connected to the output to provide a known voltage at the output while it is in the high-impedance state. The value of the resistor will depend on multiple factors, including parasitic capacitance and power consumption limitations. Typically, a 10kΩ resistor can be used to meet these requirements.

Unused 3-state CMOS outputs should be left disconnected.

6.3.2 Latching Logic

This device includes latching logic circuitry. Latching circuits commonly include D-type latches and D-type flip-flops, but include all logic circuits that act as volatile memory.

When the device is powered on, the state of each latch is unknown. There is no default state for each latch at start-up.

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The output state of each latching logic circuit only remains stable as long as power is applied to the device within the supply voltage range specified in the *Recommended Operating Conditions* table.

6.3.3 Standard CMOS Inputs

This device includes standard CMOS inputs. Standard CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics*, using Ohm's law (R = V ÷ I).

Standard CMOS inputs require that input signals transition between valid logic states quickly, as defined by the input transition time or rate in the *Recommended Operating Conditions* table. Failing to meet this specification will result in excessive power consumption and could cause oscillations. More details can be found in *Implications of Slow or Floating CMOS Inputs*.

Do not leave standard CMOS inputs floating at any time during operation. Unused inputs must be terminated at V_{CC} or GND. If a system will not be actively driving an input at all times, then a pull-up or pull-down resistor can be added to provide a valid input voltage during these times. The resistor value will depend on multiple factors; a 10kΩ resistor, however, is recommended and will typically meet all requirements.

6.3.4 Clamp Diode Structure

As shown in Figure 6-2, the inputs and outputs to this device have both positive and negative clamping diodes.

CAUTION

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

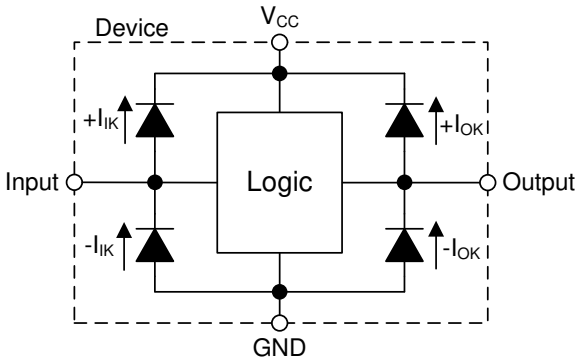

Figure 6-2. Electrical Placement of Clamping Diodes for Each Input and Output

6.4 Device Functional Modes

Table 6-1. Function Table (Each Latch)

INPUTS(1)			OUTPUT(2) Q
OE	LE	D	
L	H	H	H
L	H	L	L
L	L	X	Q_0
H	X	X	Z

(1) H = High voltage level, L = Low voltage level, X = High or low voltage level
(2) H = Driving high, L = Driving low, Q_0 = Driving previous high or low state, Z = High impedance

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7 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

7.1 Application Information

The SN74AC573-Q1 can be used to drive signals over relatively long traces or transmission lines. A series damping resistor placed in series with the transmitter's output can be used to reduce ringing caused by impedance mismatches between the driver, transmission line, and receiver. The figure in the *Application Curve* section shows the received signal with three separate resistor values. Just a small amount of resistance can make a significant impact on signal integrity in this type of application.

7.2 Typical Application

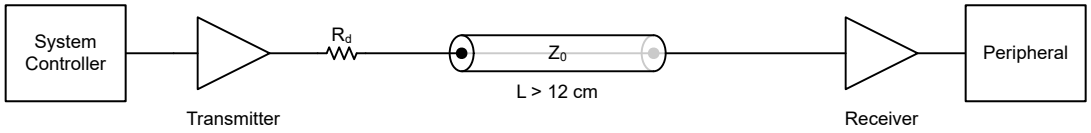

Figure 7-1. Typical Application Block Diagram

7.3 Design Requirements

7.3.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics of the device as described in the *Electrical Characteristics* section.

The positive voltage supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74AC573-Q1 plus the maximum static supply current, I_{CC}, listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only source as much current that is provided by the positive supply source. Ensure the maximum total current through V_{CC} listed in the *Absolute Maximum Ratings* is not exceeded.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74AC573-Q1 plus the maximum supply current, I_{CC}, listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only sink as much current that can be sunk into its ground connection. Ensure the maximum total current through GND listed in the *Absolute Maximum Ratings* is not exceeded.

The SN74AC573-Q1 can drive a load with a total capacitance less than or equal to 50pF while still meeting all of the data sheet specifications. Larger capacitive loads can be applied; however, it is not recommended to exceed 50pF.

The SN74AC573-Q1 can drive a load with total resistance described by $R_L \geq V_O / I_O$, with the output voltage and current defined in the *Electrical Characteristics* table with V_{OH} and V_{OL}. When outputting in the HIGH state, the output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the V_{CC} pin.

Total power consumption can be calculated using the information provided in *CMOS Power Consumption and Cpd Calculation*.

Thermal increase can be calculated using the information provided in *Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices*.

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CAUTION

The maximum junction temperature, $T_{J(max)}$ listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

7.3.2 Input Considerations

Input signals must cross $V_{IL(max)}$ to be considered a logic LOW, and $V_{IH(min)}$ to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either V_{CC} or ground. The unused inputs can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input will be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The drive current of the controller, leakage current into the SN74AC573-Q1 (as specified in the *Electrical Characteristics*), and the desired input transition rate limits the resistor size. A 10kΩ resistor value is often used due to these factors.

The SN74AC573-Q1 has CMOS inputs and thus requires fast input transitions to operate correctly, as defined in the *Recommended Operating Conditions* table. Slow input transitions can cause oscillations, additional power consumption, and reduction in device reliability.

Refer to the *Feature Description* section for additional information regarding the inputs for this device.

7.3.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the V_{OH} specification in the *Electrical Characteristics*. The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OL} specification in the *Electrical Characteristics*.

Push-pull outputs that could be in opposite states, even for a very short time period, should never be connected directly together. This can cause excessive current and damage to the device.

Two channels within the same device with the same input signals can be connected in parallel for additional output drive strength.

Unused outputs can be left floating. Do not connect outputs directly to V_{CC} or ground.

Refer to the *Feature Description* section for additional information regarding the outputs for this device.

7.4 Detailed Design Procedure

1. Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. An example layout is shown in the *Layout* section.
2. Ensure the capacitive load at the output is ≤ 50pF. This is not a hard limit; by design, however, it will optimize performance. This can be accomplished by providing short, appropriately sized traces from the SN74AC573-Q1 to one or more of the receiving devices.
3. Ensure the resistive load at the output is larger than (V_{CC} / $I_{O(max)}$)Ω. Doing this will prevent the maximum output current from the *Absolute Maximum Ratings* from being violated. Most CMOS inputs have a resistive load measured in MΩ; much larger than the minimum calculated previously.
4. Thermal issues are rarely a concern for logic gates; the power consumption and thermal increase, however, can be calculated using the steps provided in the application report, *CMOS Power Consumption and Cpd Calculation*.

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7.5 Application Curve

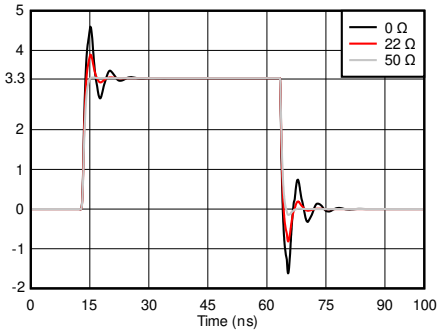

Figure 7-2. Simulated Signal Integrity at the Receiver with Different Damping Resistor (R_d) Values

7.6 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. A 0.1µF capacitor is recommended for this device. It is acceptable to parallel multiple bypass capacitors to reject different frequencies of noise. The 0.1µF and 1µF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

7.7 Layout

7.7.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices, inputs must never be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC}, whichever makes more sense for the logic function or is more convenient.

7.7.2 Layout Example

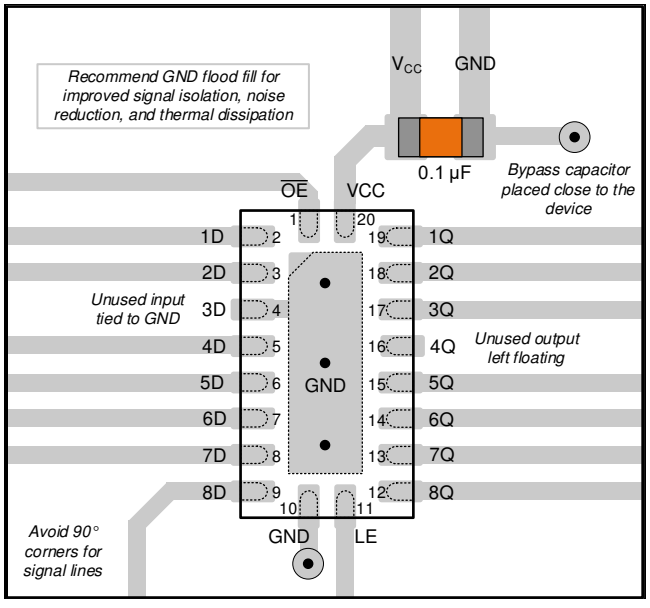

Figure 7-3. Example Layout for the SN74AC573-Q1 in the RKS Package

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8 Device and Documentation Support

8.1 Documentation Support

8.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, *CMOS Power Consumption and Cpd Calculation*
- Texas Instruments, *Implications of Slow or Floating CMOS Inputs*
- Texas Instruments, *Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices*

8.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

8.3 Support Resources

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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8.5 Electrostatic Discharge Caution

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

8.6 Glossary

TI Glossary	This glossary lists and explains terms, acronyms, and definitions.

9 Revision History

Changes from Revision * (November 2023) to Revision A (March 2024)	Page
• Added PW package to *Device Information* table, *Pin Configuration and Functions* section and *Thermal Information* table	1

10 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74AC573QPWRQ1	ACTIVE	TSSOP	PW	20	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AC573Q	Samples
SN74AC573QWRKSRQ1	ACTIVE	VQFN	RKS	20	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AC573Q	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF SN74AC573-Q1 :

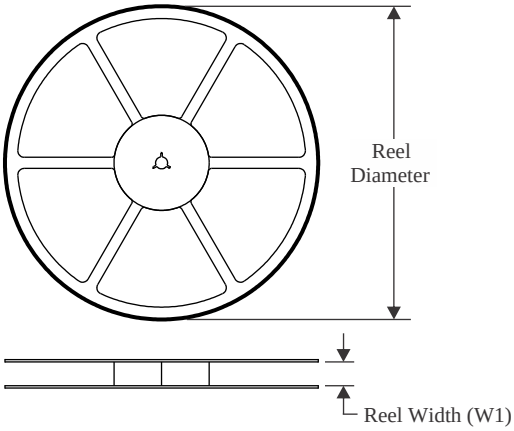
- Catalog : SN74AC573

NOTE: Qualified Version Definitions:

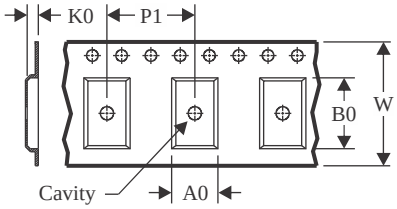
- Catalog - TI's standard catalog product

TAPE AND REEL INFORMATION

REEL DIMENSIONS

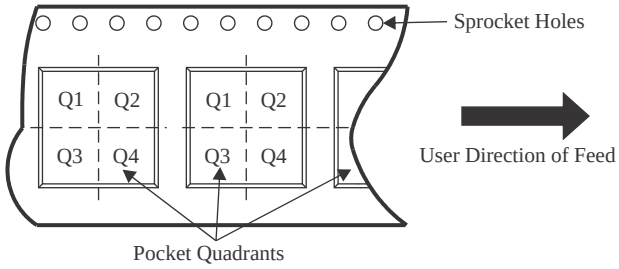


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

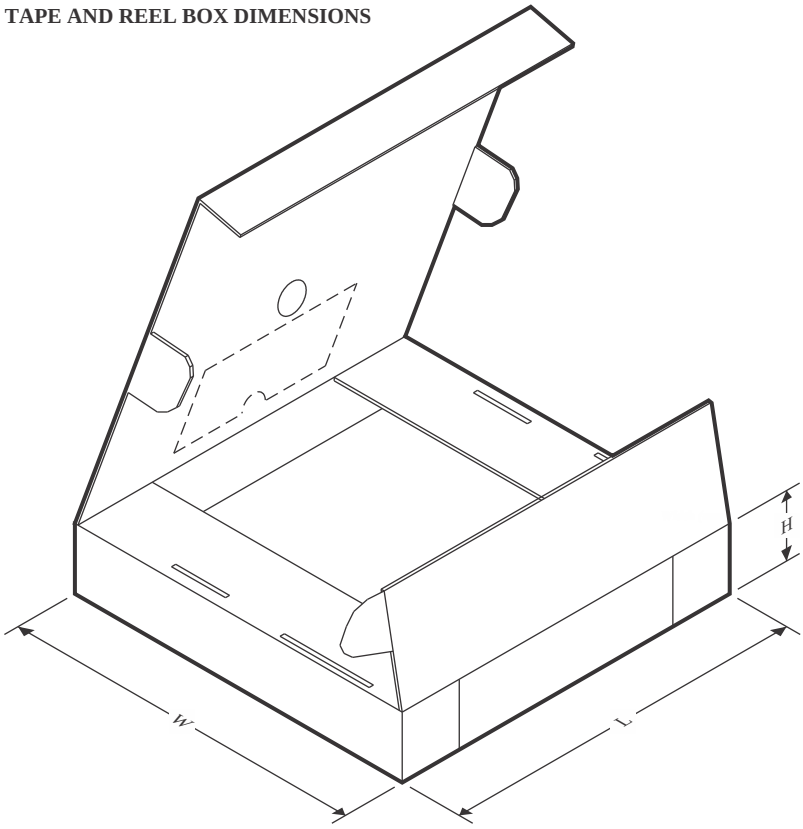
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74AC573QPWRQ1	TSSOP	PW	20	3000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1
SN74AC573QWRKSRQ1	VQFN	RKS	20	3000	180.0	12.4	2.8	4.8	1.2	4.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

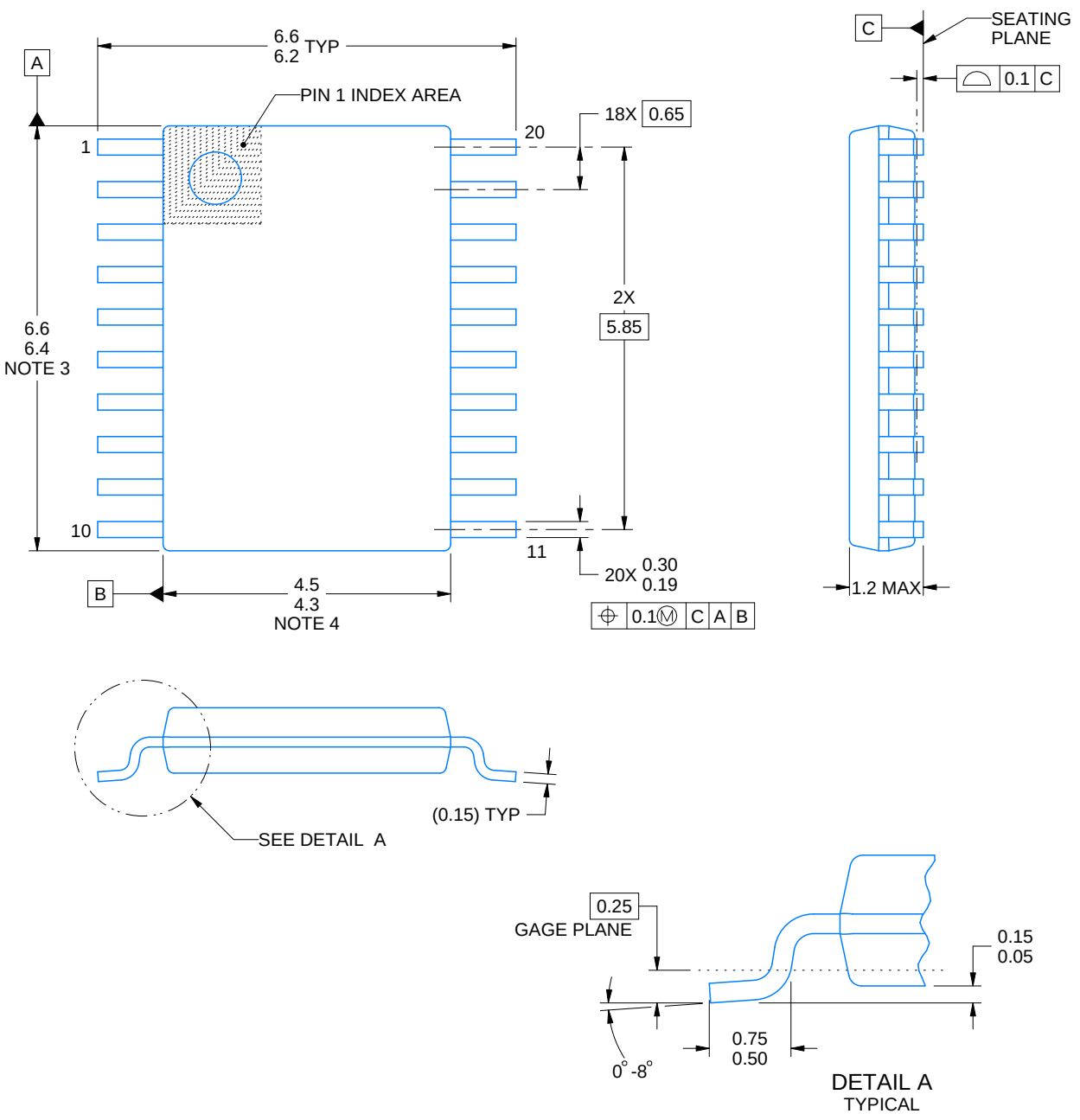
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74AC573QPWRQ1	TSSOP	PW	20	3000	353.0	353.0	32.0
SN74AC573QWRKSRQ1	VQFN	RKS	20	3000	210.0	185.0	35.0

PACKAGE OUTLINE

PW0020A

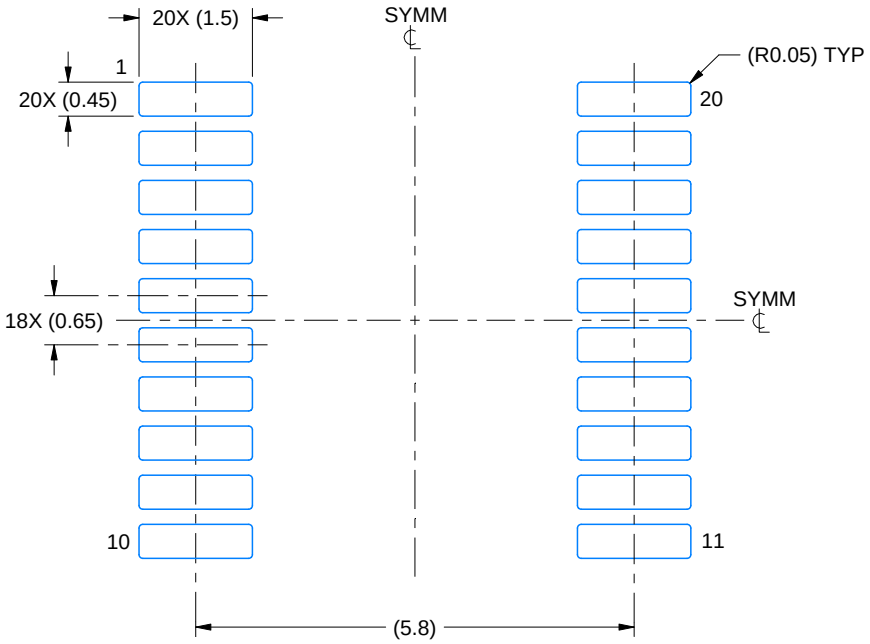
TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.



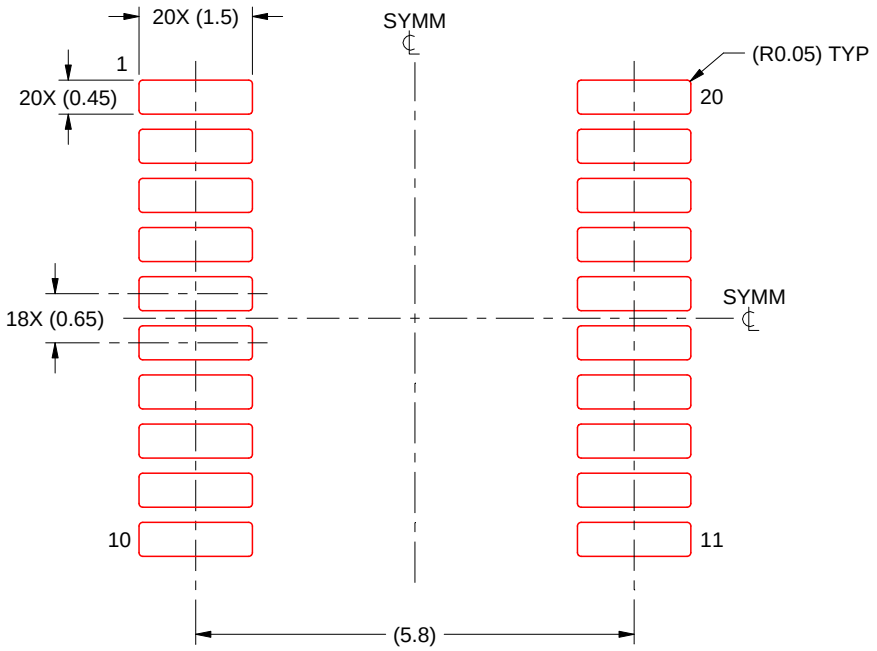
LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X

SOLDER MASK DETAILS

4220206/A 02/2017

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220206/A 02/2017

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

GENERIC PACKAGE VIEW

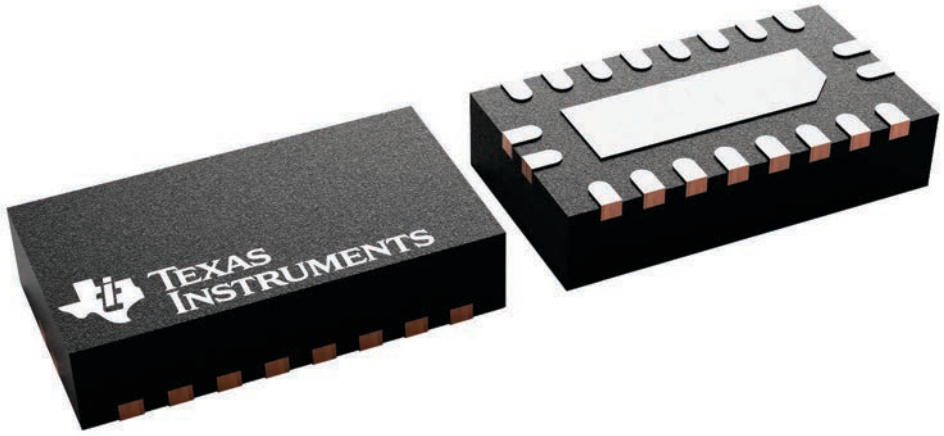
RKS 20

VQFN - 1 mm max height

2.5 x 4.5, 0.5 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

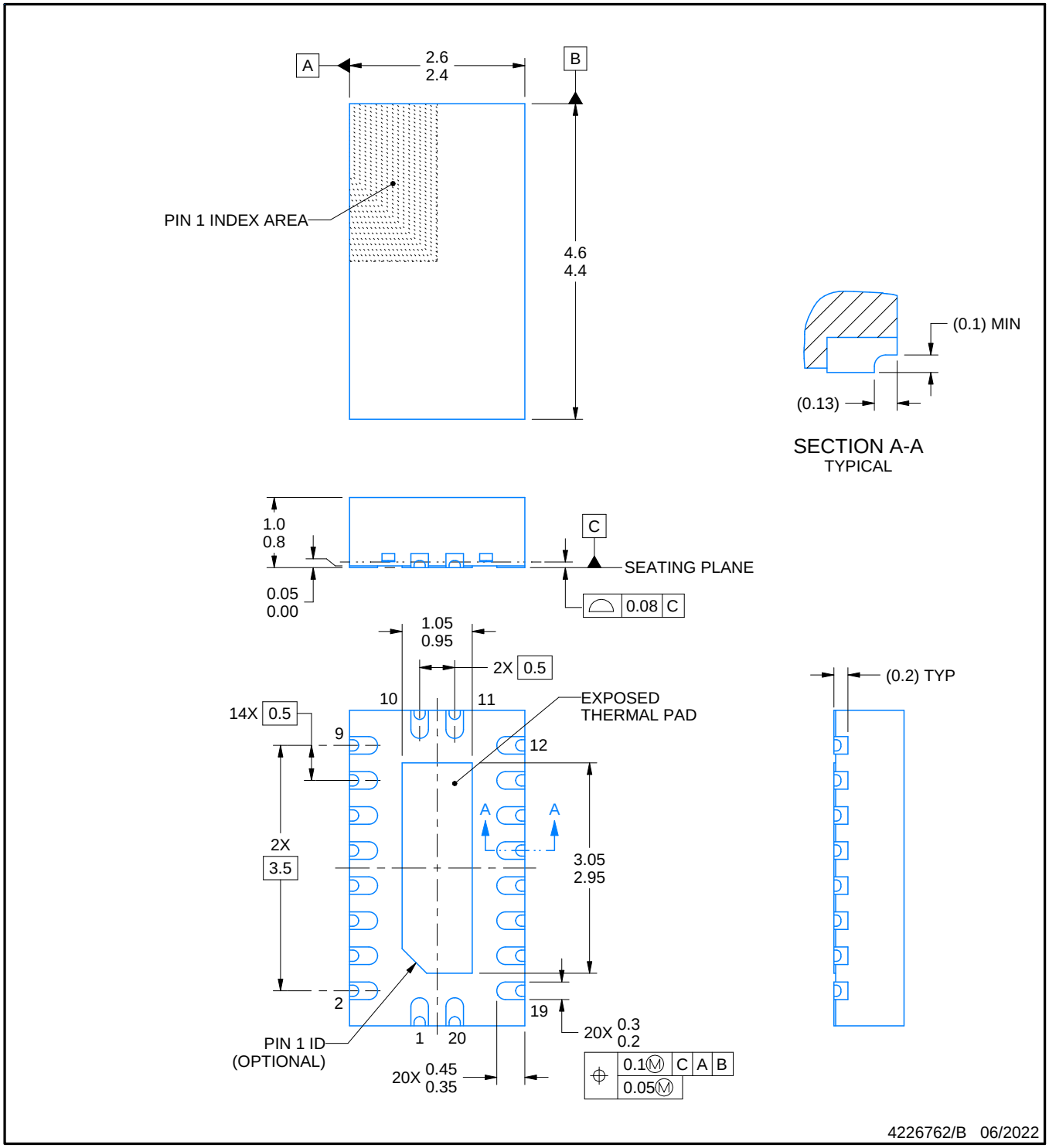


RKS0020B

PACKAGE OUTLINE

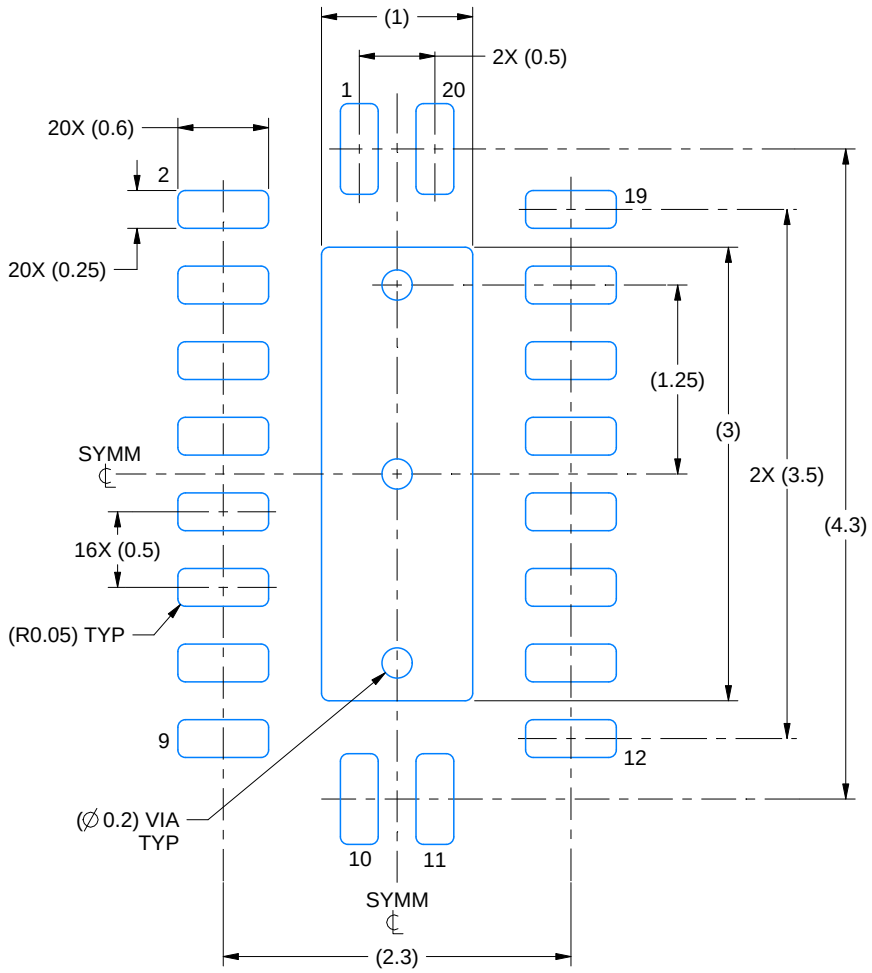
VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



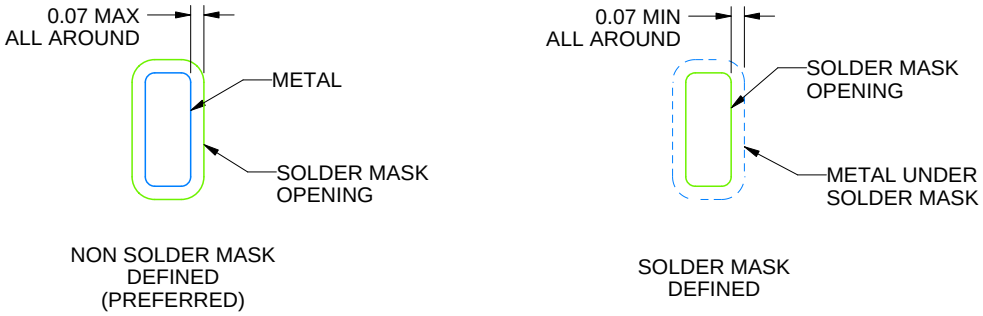
NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



LAND PATTERN EXAMPLE

SCALE:20X

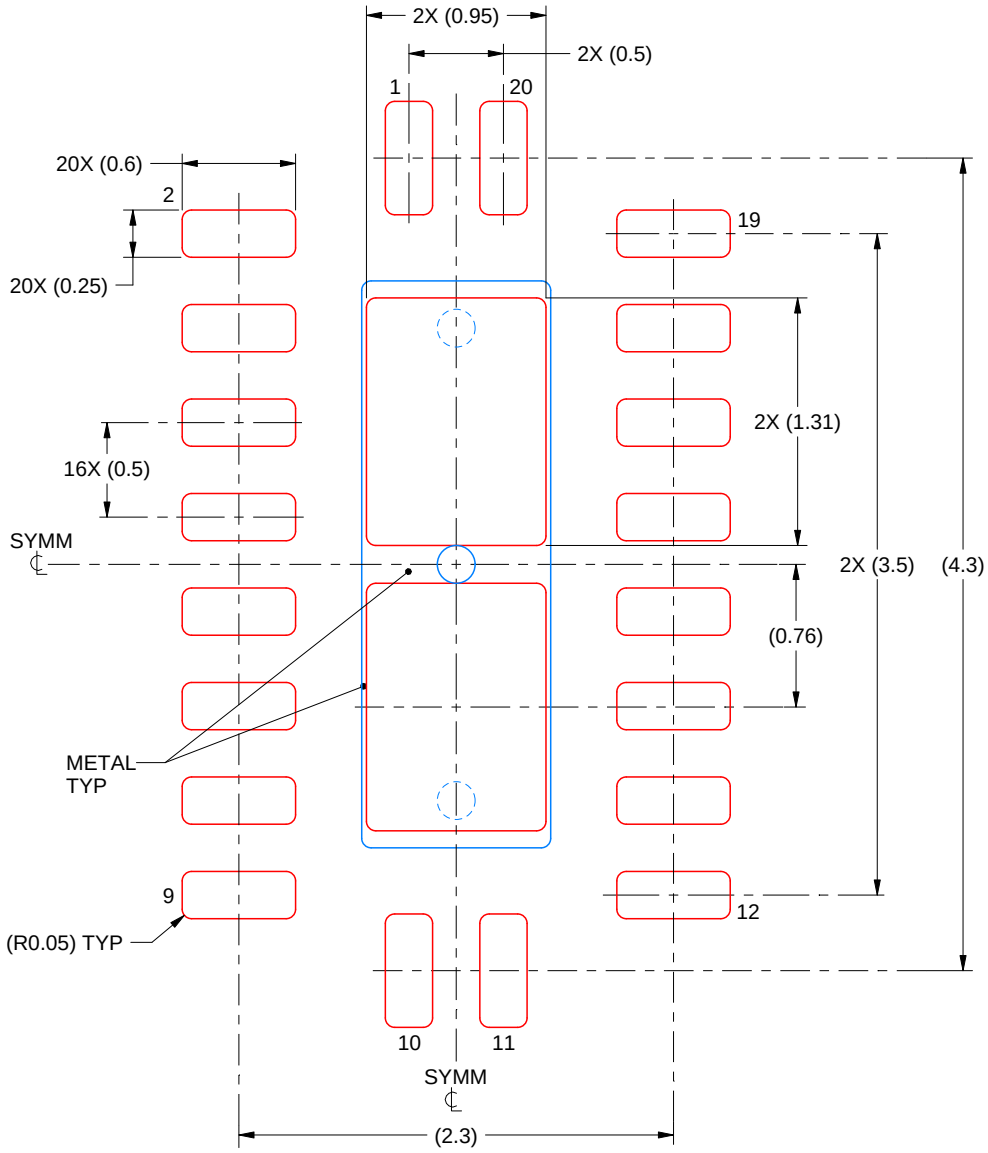


SOLDER MASK DETAILS

4226762/B 06/2022

NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
5. Vias are optional depending on application, refer to device data sheet. If some or all are implemented, recommended via locations are shown.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD
83% PRINTED SOLDER COVERAGE BY AREA
SCALE:25X

4226762/B 06/2022

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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